

SPECIFICATION

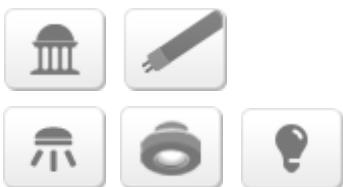
Product : STWSC12S-E2H100ZP000

Seoul Semiconductor			Customer
Drawn by	Checked by	Approved by	Approved by
Levi	Ivy	BY Han	
25.05.02	25.05.02	25.05.02	

Actualize a spectrum closest to the sunlight

Mid-Power LED – 3030 Series

STWSC12S-E2H100ZP000



Product Brief

Description

- This White Colored surface-mount LED comes in standard package dimension.
Package Size : 3.0x3.0x0.75mm
- It has a substrate made up of a molded plastic reflector sitting on top of a lead frame.
- The die is attached within the reflector cavity and the cavity is encapsulated by silicone.
- The package design coupled with careful selection of component materials allow these products to perform with high reliability.

Features and Benefits

- Thermally Enhanced Package Design
- Mid Power to up to 0.2W
- Max. Driving Current 100mA
- Compact Package Size
- High Color Quality with CRI Min.95 (R9>85)
- Pb-free Reflow Soldering Application

Key Applications

- Replacement lamps – Bulb, Tube
- Commercial
- Industrial
- Residential

Table 1. Product Selection Table

Reference P/N	Order code	Flux bin	CCT	Step	VF bin
STWSC12S-E2H100ZP000	230653SE2A	230	65:6500K	3S: 3step Mixing	E2A
	230573SE2A	230	57:5700K		E2A
	230503SE2A	230	50:5000K		E2A
	210403SE2A	210	40:4000K		E2A
	210353SE2A	210	35:3500K		E2A
	210303SE2A	210	30:3000K		E2A
	210273SE2A	210	27:2700K		E2A
Reference P/N	Order code	Flux bin	CCT	Step	VF bin
STWSC12S-E2H100ZP000	230653M000	230	65:6500K	3M: 3step Mixing	000
	230573M000	230	57:5700K		000
	230503M000	230	50:5000K		000
	210403M000	210	40:4000K		000
	210353M000	210	35:3500K		000
	210303M000	210	30:3000K		000
	210273M000	210	27:2700K		000
Reference P/N	Order code	Flux bin	CCT	Step	VF bin
STWSC12S-E2H100ZP000	230654M000	230	65:6500K	4M: 4step Mixing	000
	230574M000	230	57:5700K		000
	230504M000	230	50:5000K		000
	210404M000	210	40:4000K		000
	210354M000	210	35:3500K		000
	210304M000	210	30:3000K		000
	210274M000	210	27:2700K		000

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Performance Characteristics

Table 2. Product Selection Guide, $I_F = 65\text{mA}$, $T_j = 25^\circ\text{C}$, RH30%

Min.	Nominal	Min. Flux	Typ.	Typ.	PPF	PPE
			Luminous	Luminous		
CRI	CCT [K] ^[1]	[lm]	Flux Φ_V ^[2]	Efficacy	[$\mu\text{mol/s}$] ^[3]	[$\mu\text{mol/J}$] ^[4]
			[lm]	[lm/W]	Typ.	Typ.
95	6500	23.0	26.1	136.5	0.43	2.23
	5700	23.0	26.0	135.5	0.43	2.22
	5000	23.0	26.7	138.8	0.44	2.28
	4000	21.0	25.3	131.7	0.42	2.16
	3500	21.0	24.9	129.6	0.41	2.13
	3000	21.0	23.1	119.9	0.38	1.98
	2700	21.0	22.4	116.6	0.37	1.92

Notes :

(1) Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram.

(2) Seoul Semiconductor maintains a tolerance of $\pm 5\%$ on luminous flux.

(3) Photosynthetic Photon Flux (PPF) includes wavelengths between 400 and 700 nm.

(4) Photosynthetic Photon Efficacy (PPE) includes wavelengths between 400 and 700 nm.

Performance Characteristics

Table 3. Characteristics, $I_F=65\text{mA}$, $T_j=25^\circ\text{C}$

Parameter	Symbol	Value			Unit
		Min.	Typ.	Max.	
Forward Voltage ^[1]	V_F	2.80	2.96	3.10	V
Luminous Flux ^[1]	Φ_v	-	26.7	-	lm
Correlated Color Temperature	CCT	2,700	-	6,500	K
CRI ^[1]	Ra	95	-	-	-
Viewing Angle ^[2]	$2\Theta_{1/2}$	-	120	-	deg.
Thermal resistance (J to S) ^[3]	$R\theta_{j-s}$	-	8.0	-	K/W
ESD Sensitivity(HBM)	-	Class 3A JESD22-A114-E			

Table 4. Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Forward Current	I_F	100	mA
Power Dissipation	P_D	0.3	W
Junction Temperature	T_j	125	°C
Operating Temperature	T_{opr}	-40 ~ + 85	°C
Storage Temperature	T_{stg}	-40 ~ + 100	°C

Notes :

- (1) Tolerance : VF : $\pm 0.1\text{V}$, Flux : $\pm 5\%$, Ra : ± 2 , x,y : ± 0.005
- (2) $2\Theta_{1/2}$ is the off-axis where the luminous intensity is 1/2 of the peak intensity.
- (3) Thermal resistance : R_{thJS} (Junction / solder)
- (4) It is recommended to use it in the condition that the reliability is secured within the Max value.

- LED's properties might be different from suggested values like above and below tables if operation condition will be exceeded our parameter range. Care is to be taken that power dissipation does not exceed the absolute maximum rating of the product.
- Thermal resistance can be increased substantially depending on the heat sink design/operating condition, and the maximum possible driving current will decrease accordingly.
- All measurements were made under the standardized environment of Seoul Semiconductor.

Characteristics Graph

Fig 1. Color Spectrum, $T_j = 25^\circ\text{C}$

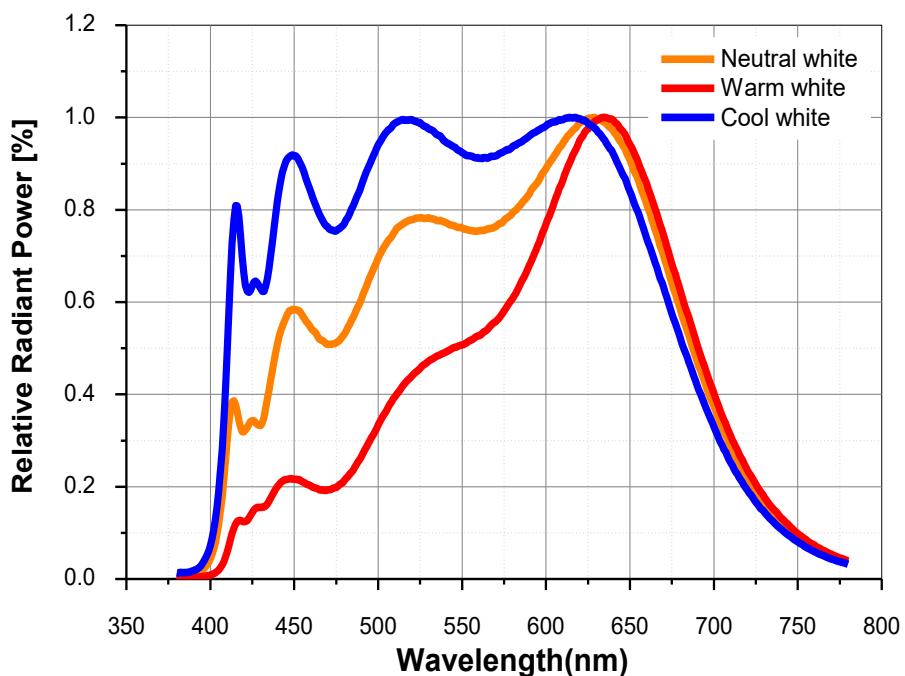
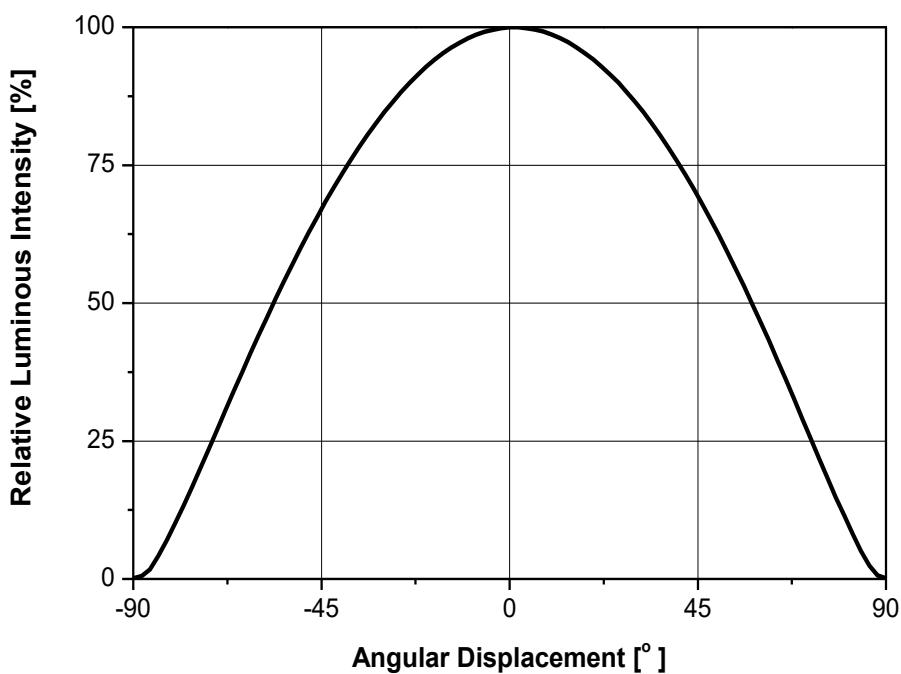


Fig 2. Radiant Pattern, $T_j = 25^\circ\text{C}$



Characteristics Graph

Fig 3. Forward Voltage vs. Forward Current, $T_j = 25^\circ\text{C}$

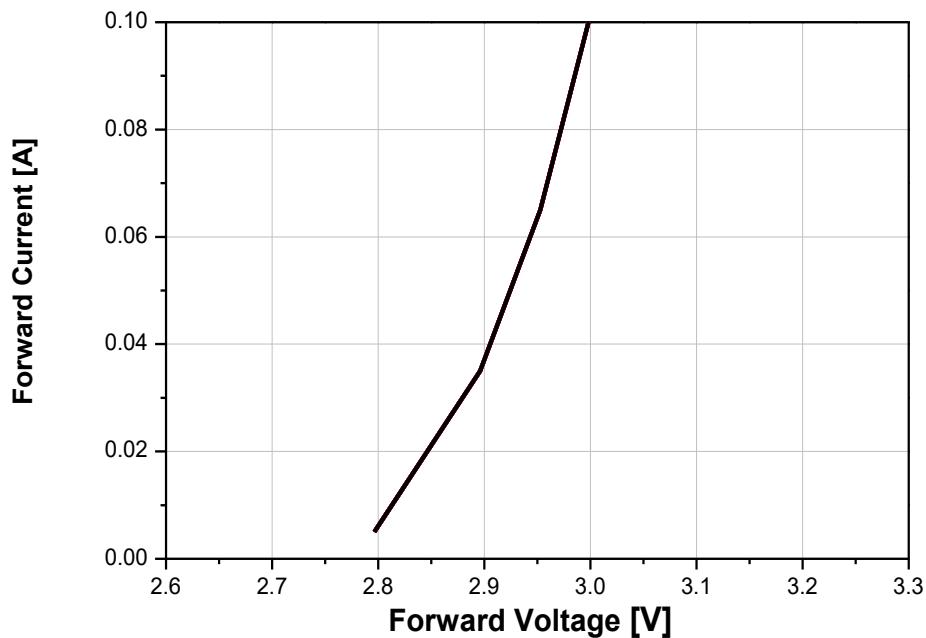
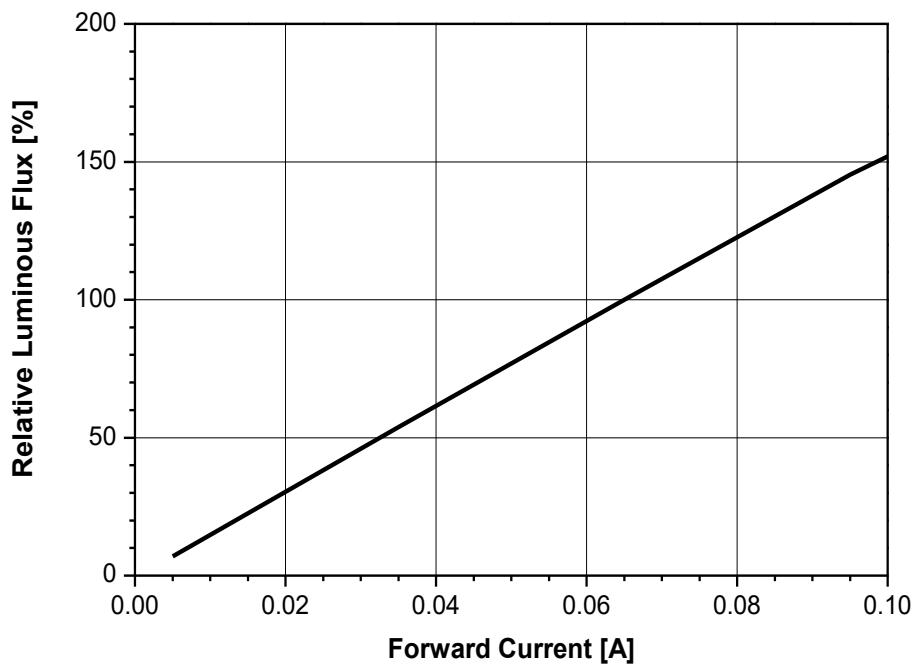
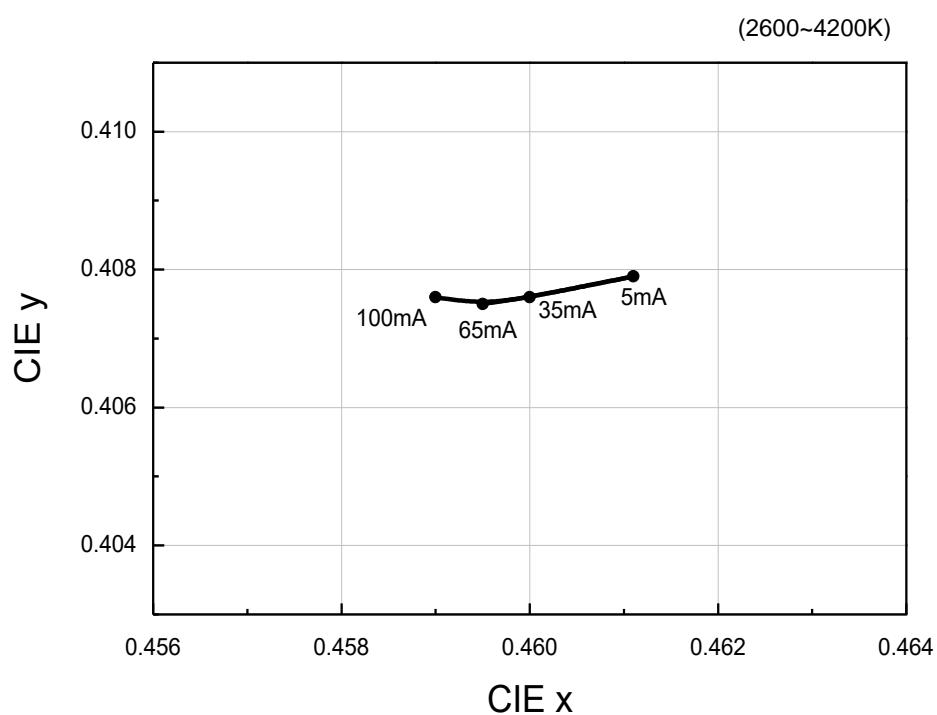
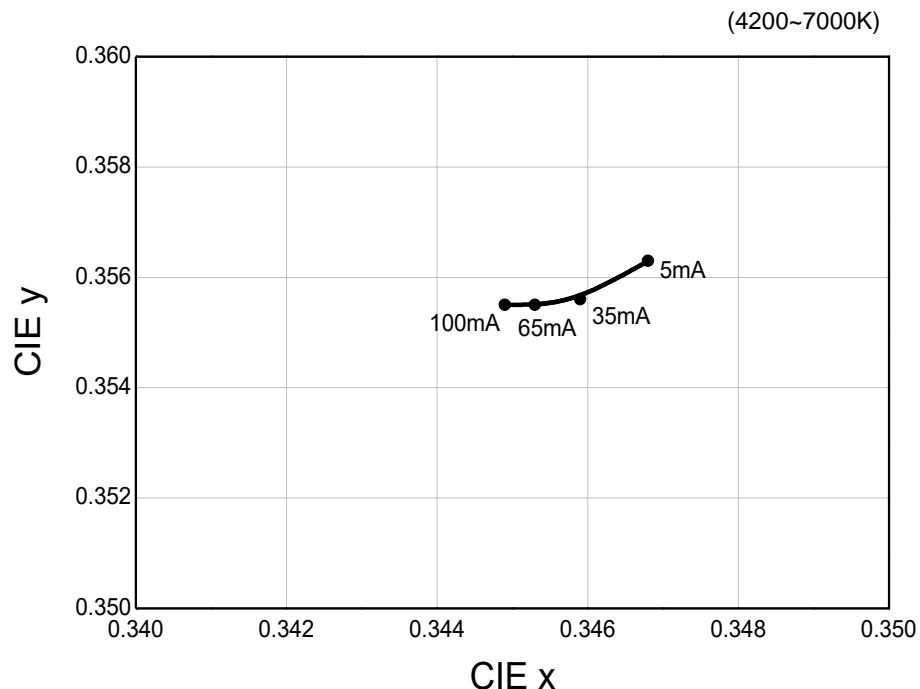


Fig 4. Forward Current vs. Relative Luminous Intensity, $T_j = 25^\circ\text{C}$



Characteristics Graph

Fig 5. Forward Current vs. CIE x, y Shift, $T_j = 25^\circ\text{C}$



Characteristics Graph

Fig 6. Junction Temperature vs. Relative Luminous Intensity, $I_F=65\text{mA}$

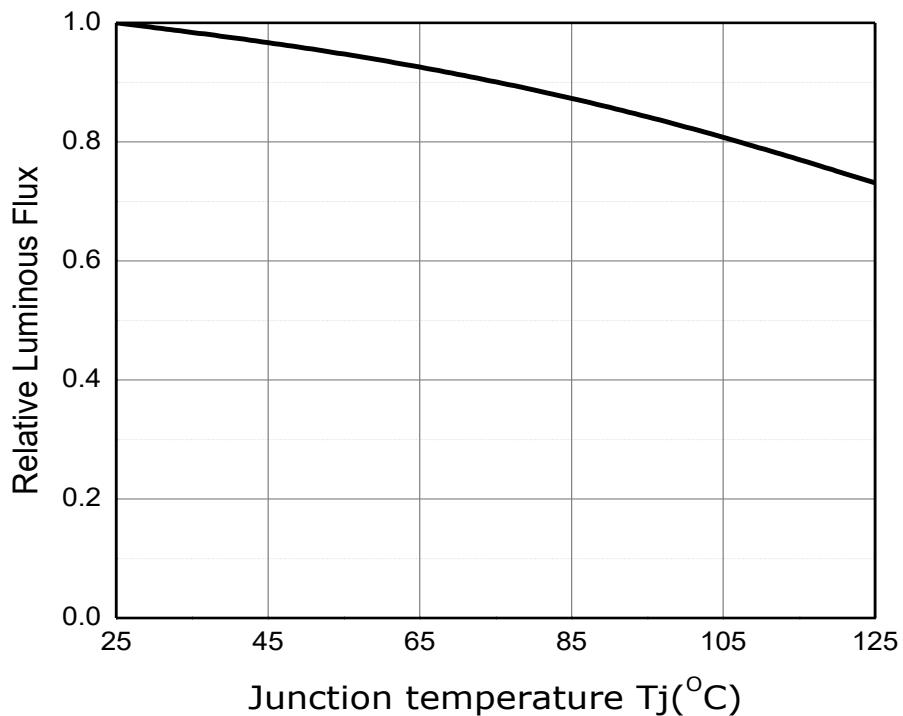
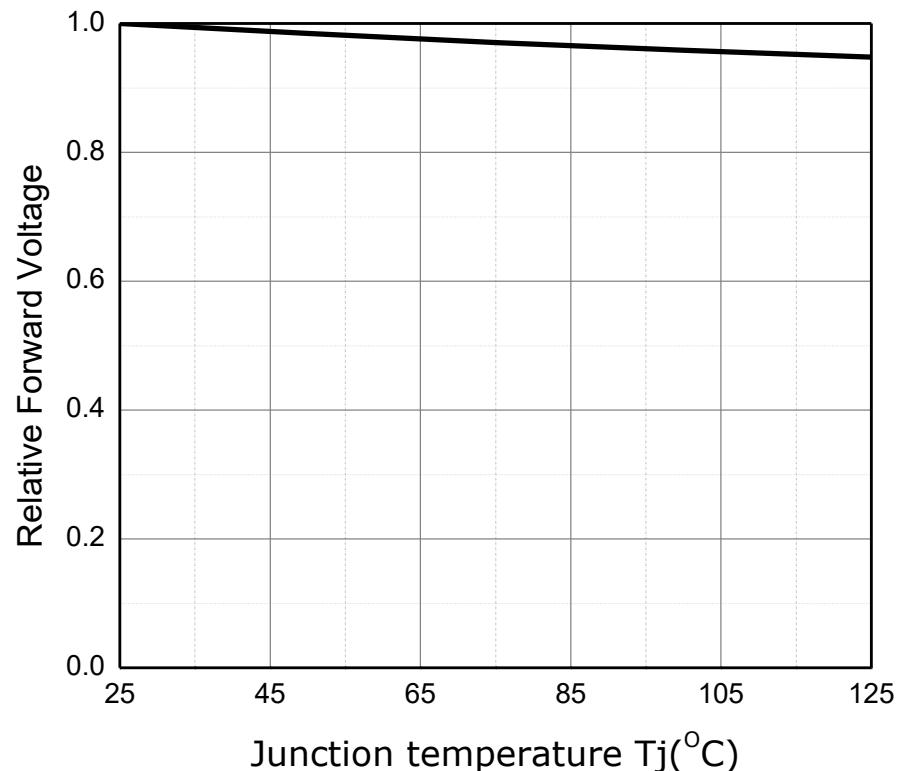
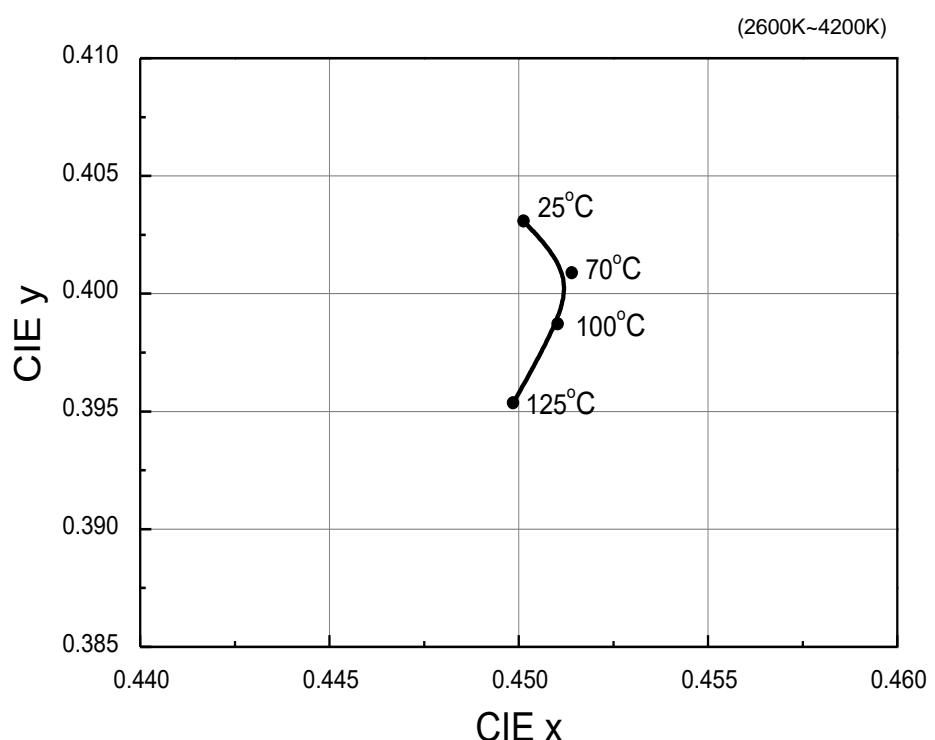
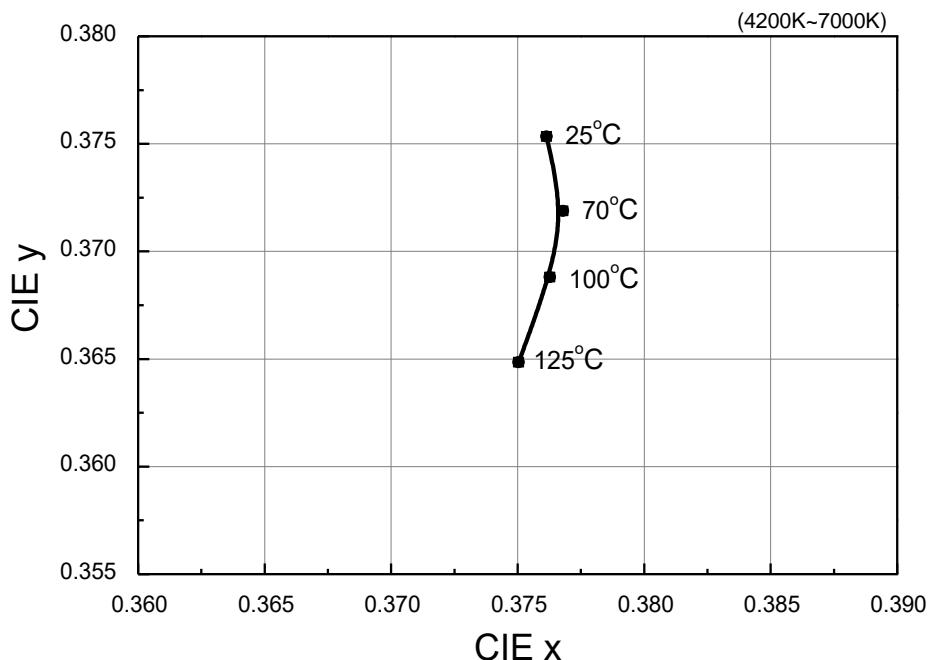


Fig 7. Junction Temperature vs. Relative Forward Voltage, $I_F=65\text{mA}$



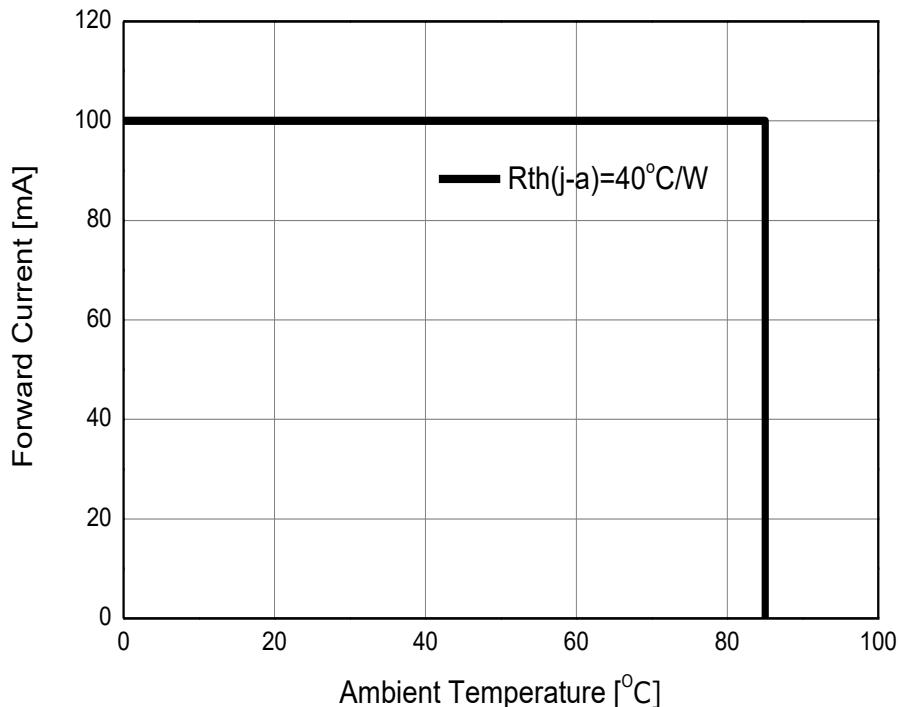
Characteristics Graph

Fig 8. Chromaticity Coordinate vs. Junction Temperature, $I_F=65\text{mA}$



Characteristics Graph

Fig 9. Ambient Temperature vs. Maximum Forward Current, $T_{j_{\max}} = 125^{\circ}\text{C}$



Color Bin Structure

Table 5. Bin Code description, $T_j=25^\circ\text{C}$, $I_F=65\text{mA}$

Part Number	Luminous Flux (lm)			Color Chromaticity Coordinate	Typical Forward Voltage (V)		
	Bin Code	Min.	Max.		Bin Code	Min.	Max.
STWSC12S-E2H10000	210	21.0	23.0	Refer to page. 12 ~ 20	E2A	2.85	2.95
	230	23.0	25.0		E2B	2.95	3.00
	250	25.0	27.0				
	270	27.0	29.0				

Table 6. Intensity rank distribution

 Available ranks

CCT	CIE	Flux Rank			
6000 ~ 7000K	A	210	230	250	270
5300 ~ 6000K	B	210	230	250	270
4700 ~ 5300K	C	210	230	250	270
3700 ~ 4200K	E	210	230	250	270
3200 ~ 3700K	F	210	230	250	270
2900 ~ 3200K	G	210	230	250	270
2600 ~ 2900K	H	210	230	250	270

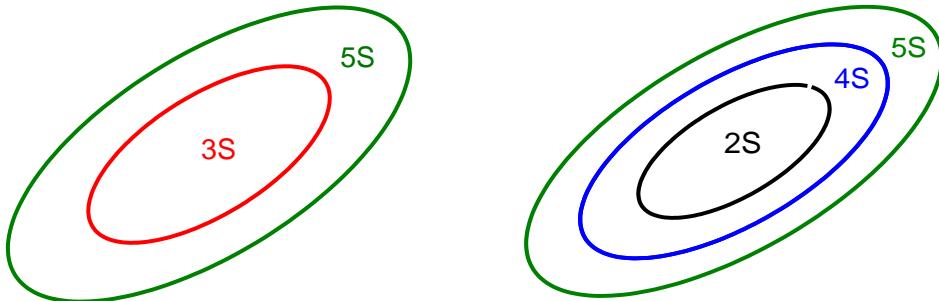
*Notes :

All measurements were made under the standardized environment of Seoul Semiconductor.

In order to ensure availability, single color rank will not be orderable.

Color Bin Structure

CIE Chromaticity Diagram (Cool White), $T_a=25^\circ\text{C}$, $I_F=150\text{mA}$



Order	Box Packing Method
xx3S	3S(3step) Single
xx4M	3S(3step) & 5S (5step) Mixing

Order	Box Packing Method
xx3M	2S(2.3step) & 4S(3.7step) Mixing
xx4M	2S(2.3step) & 5S(5step) Mixing

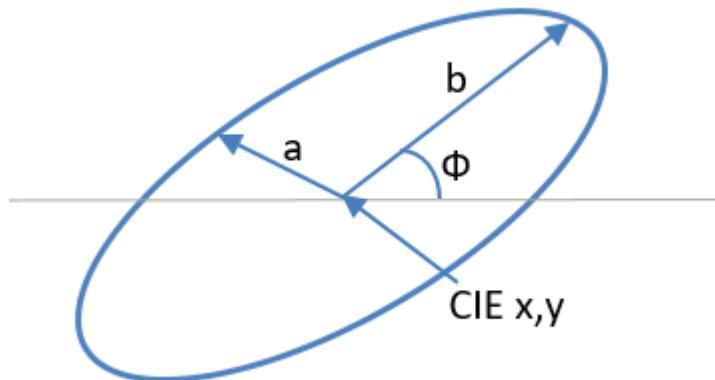
*Notes :

1. xx3S Order will ship 3S (=also include 2S)
2. xx3M Order will ship 2S & 4S Mixing (=also include 2S and 3S)
3. xx4M Order will ship 3S & 5S Or 2S & 5S Mixing (=also include 2S, 3S and 3M)
4. Doughnut Bin will not ship alone (=Will ship with mixing bin)

* 'xx' can be 65=6500K, 56=5600K, 50=5000K, 40=4000K, 30=3000K, 27= 2700K

Color Bin Structure

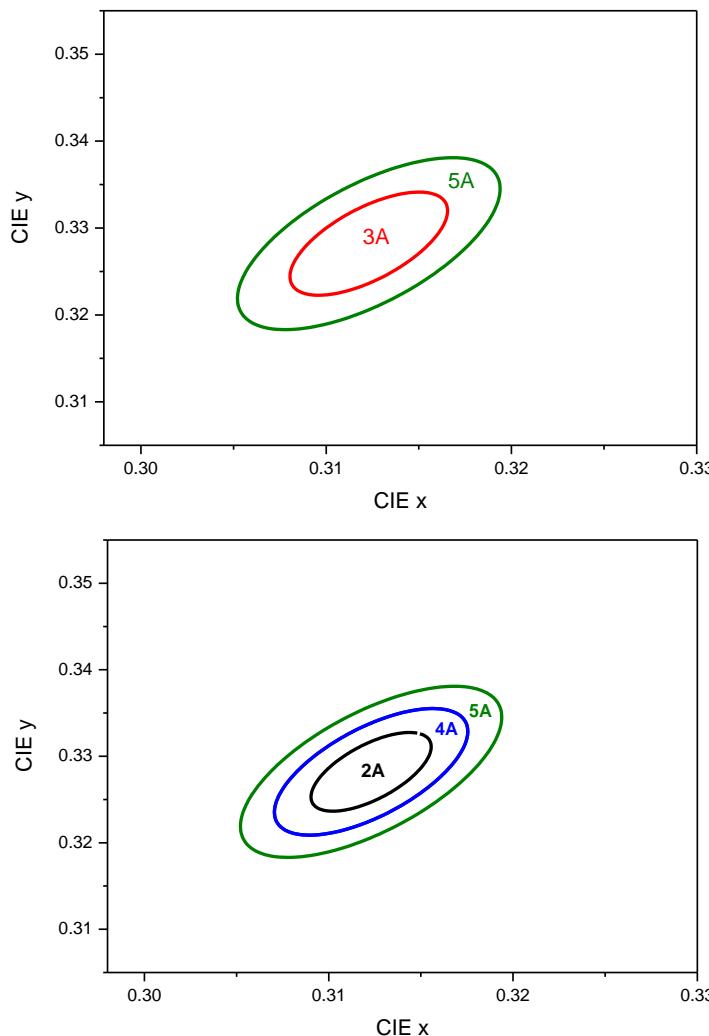
CIE Chromaticity Diagram (Cool White), $T_a=25^\circ\text{C}$, $I_F=65\text{mA}$



Macadam	CCT	Center Point		Major Axis	Minor Axis	Rotation Angle
	(K)	CIE x	CIE y	a	b	Φ
3 step	2700	0.4578	0.4101	0.0081	0.0042	54
	3000	0.4338	0.403	0.0083	0.0040	53
	3500	0.4073	0.3917	0.0093	0.0042	54
	4000	0.3818	0.3797	0.0094	0.0040	54
	5000	0.3447	0.3553	0.0082	0.0035	60
	5700	0.3287	0.3417	0.0076	0.0033	59
	6500	0.3123	0.3282	0.0067	0.0029	59
5 step	2700	0.4578	0.4101	0.0135	0.0070	54
	3000	0.4338	0.403	0.0140	0.0068	53
	3500	0.4073	0.3917	0.0155	0.0069	54
	4000	0.3818	0.3797	0.0156	0.0068	54
	5000	0.3447	0.3553	0.0137	0.0058	60
	5700	0.3287	0.3417	0.0125	0.0053	59
	6500	0.3123	0.3282	0.0112	0.0048	59

Color Bin Structure

CIE Chromaticity Diagram (Cool White), $T_a=25^\circ\text{C}$, $I_F=65\text{mA}$, CCT=6500K

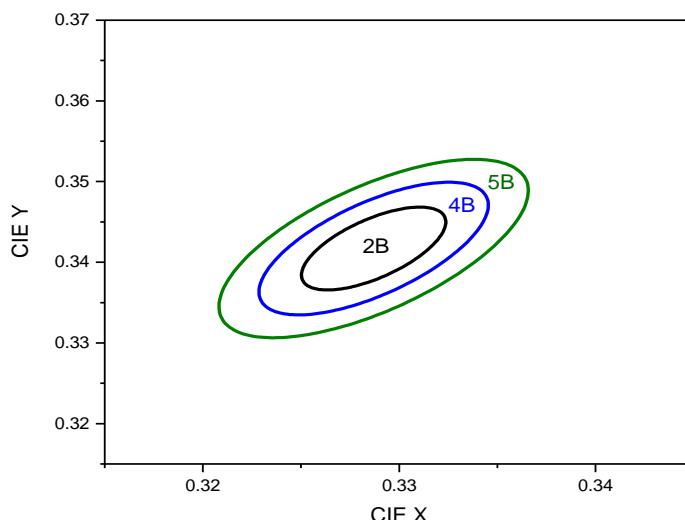
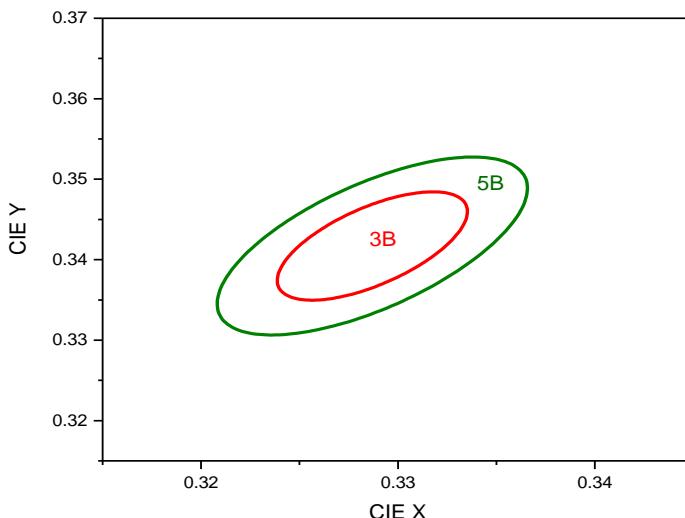


2A (2.3Step)		3A (3.0step)	
Center point	0.3123 : 0.3282	Center point	0.3123 : 0.3282
Major Axis a	0.0051	Major Axis a	0.0067
Minor Axis b	0.0022	Minor Axis b	0.0029
Ellipse Rotation Angle	59	Ellipse Rotation Angle	59

4A (3.7step)		5A (5.0Step)	
Center point	0.3123 : 0.3282	Center point	0.3123 : 0.3282
Major Axis a	0.0083	Major Axis a	0.0112
Minor Axis b	0.0036	Minor Axis b	0.0048
Ellipse Rotation Angle	59	Ellipse Rotation Angle	59

Color Bin Structure

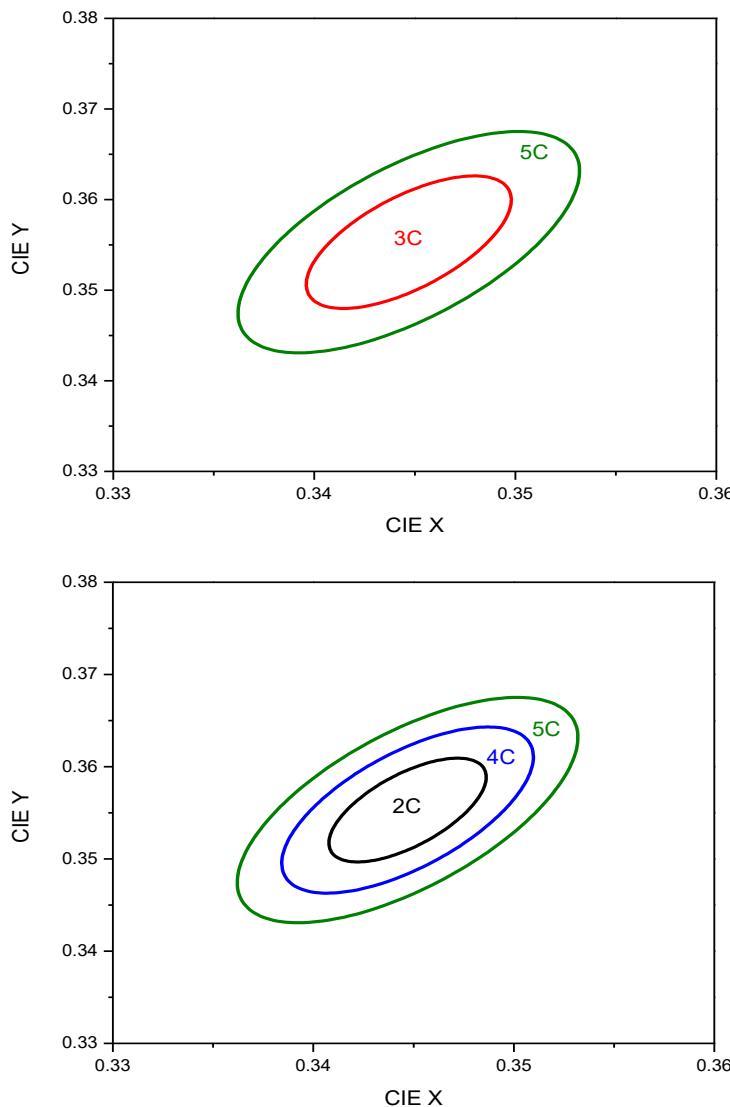
CIE Chromaticity Diagram (Cool White), $T_a=25^\circ\text{C}$, $I_F=65\text{mA}$, CCT=5700K



2B (2.3Step)		3B (3.0step)	
Center point	0.3287 : 0.3417	Center point	0.3287 : 0.3417
Major Axis a	0.0058	Major Axis a	0.0076
Minor Axis b	0.0025	Minor Axis b	0.0033
Ellipse Rotation Angle		Ellipse Rotation Angle	
59		59	
4B (3.7step)		5B (5.0Step)	
Center point	0.3287 : 0.3417	Center point	0.3287 : 0.3417
Major Axis a	0.0093	Major Axis a	0.0125
Minor Axis b	0.0039	Minor Axis b	0.0053
Ellipse Rotation Angle		Ellipse Rotation Angle	
59		59	

Color Bin Structure

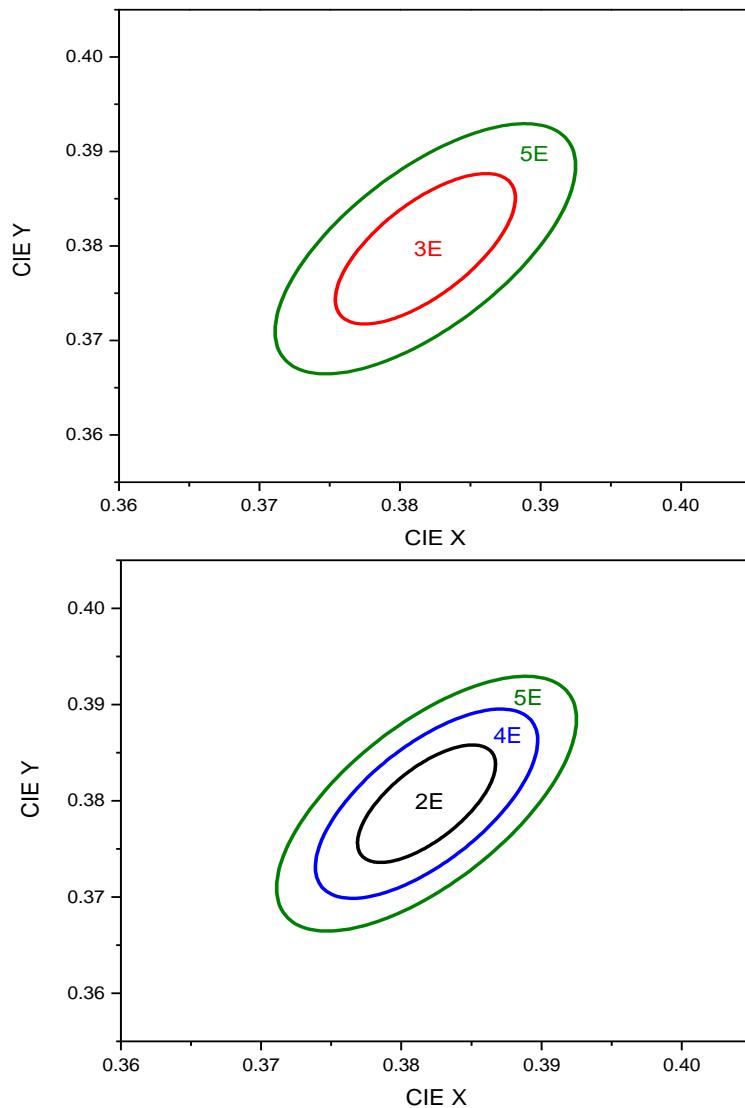
CIE Chromaticity Diagram (Cool White), $T_a=25^\circ\text{C}$, $I_F=65\text{mA}$, CCT=5000K



2C (2.3Step)		3C(3.0step)	
Center point	0.3447 : 0.3553	Center point	0.3447 : 0.3553
Major Axis a	0.0063	Major Axis a	0.0082
Minor Axis b	0.0027	Minor Axis b	0.0035
Ellipse Rotation Angle	60	Ellipse Rotation Angle	60
4C (3.7step)		5C (5.0Step)	
Center point	0.3447 : 0.3553	Center point	0.3447 : 0.3553
Major Axis a	0.0101	Major Axis a	0.0137
Minor Axis b	0.0043	Minor Axis b	0.0058
Ellipse Rotation Angle	60	Ellipse Rotation Angle	60

Color Bin Structure

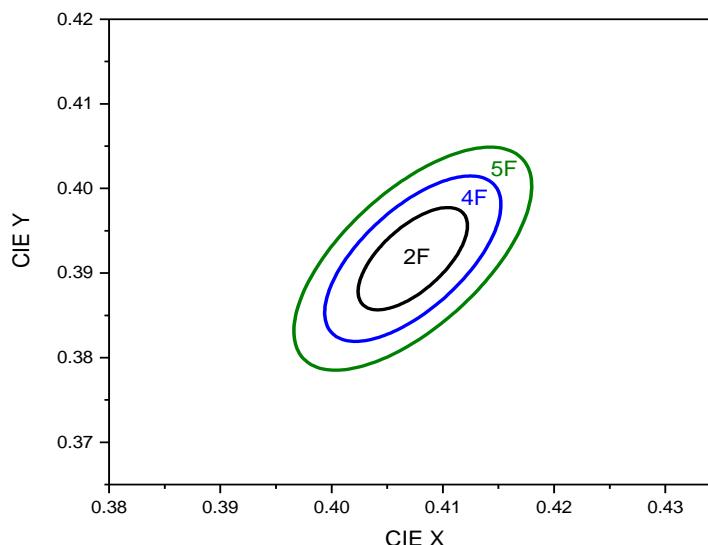
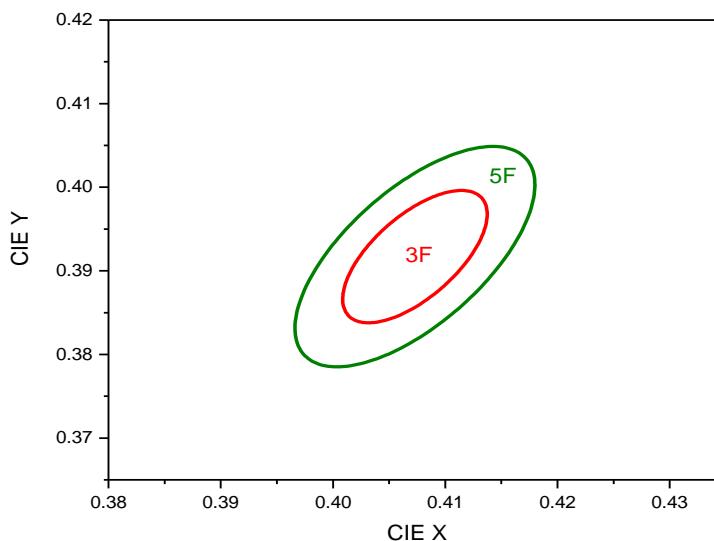
CIE Chromaticity Diagram (Neutral White), $T_a=25^\circ\text{C}$, $I_F=65\text{mA}$, CCT=4000K



2E (2.3Step)		3E(3.0step)	
Center point	0.3818 : 0.3797	Center point	0.3818 : 0.3797
Major Axis a	0.0072	Major Axis a	0.0094
Minor Axis b	0.0031	Minor Axis b	0.0040
Ellipse Rotation Angle	54	Ellipse Rotation Angle	54
4E(3.7step)		5E (5.0Step)	
Center point	0.3818 : 0.3797	Center point	0.3818 : 0.3797
Major Axis a	0.0116	Major Axis a	0.0156
Minor Axis b	0.0050	Minor Axis b	0.0068
Ellipse Rotation Angle	54	Ellipse Rotation Angle	54

Color Bin Structure

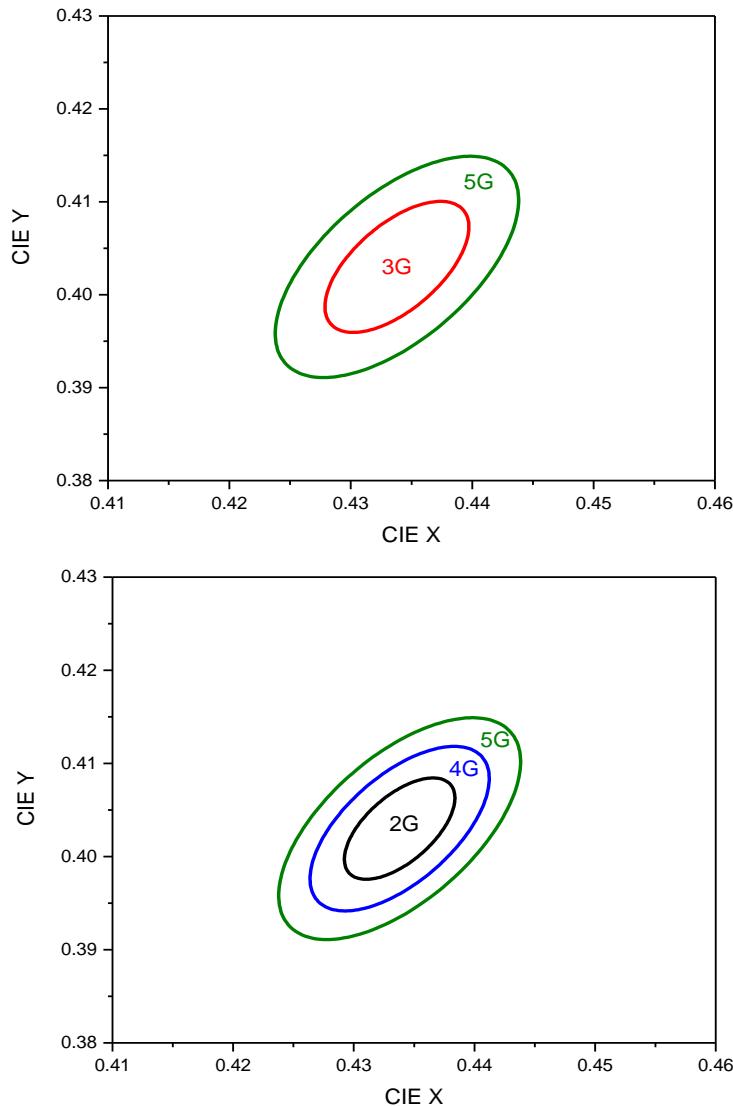
CIE Chromaticity Diagram (Warm White), $T_a=25^\circ\text{C}$, $I_F=65\text{mA}$, CCT=3500K



2F (2.3Step)		3F (3.0step)	
Center point	0.4073 : 0.3917	Center point	0.4073 : 0.3917
Major Axis a	0.0071	Major Axis a	0.0093
Minor Axis b	0.0032	Minor Axis b	0.0042
Ellipse Rotation Angle	54	Ellipse Rotation Angle	54
4F (3.7step)		5F (5.0Step)	
Center point	0.4073 : 0.3917	Center point	0.4073 : 0.3917
Major Axis a	0.0115	Major Axis a	0.0155
Minor Axis b	0.0051	Minor Axis b	0.0069
Ellipse Rotation Angle	54	Ellipse Rotation Angle	54

Color Bin Structure

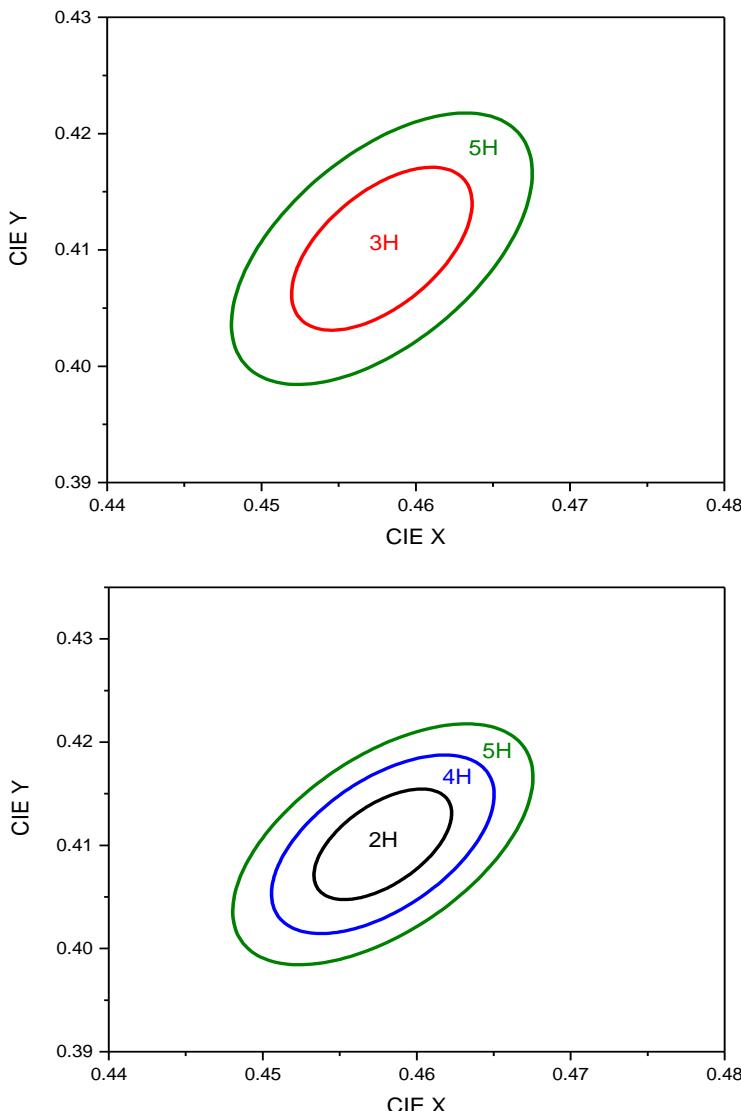
CIE Chromaticity Diagram (Warm White), $T_a=25^\circ\text{C}$, $I_F=65\text{mA}$, CCT=3000K



2G (2.3Step)		3G (3.0step)	
Center point	0.4338 : 0.4030	Center point	0.4338 : 0.4030
Major Axis a	0.0064	Major Axis a	0.0083
Minor Axis b	0.0031	Minor Axis b	0.0040
Ellipse Rotation Angle		Ellipse Rotation Angle	
53		53	
4G 3.7step)		5G (5.0Step)	
Center point	0.4338 : 0.4030	Center point	0.4338 : 0.4030
Major Axis a	0.0104	Major Axis a	0.0140
Minor Axis b	0.0050	Minor Axis b	0.0068
Ellipse Rotation Angle		Ellipse Rotation Angle	
53		53	

Color Bin Structure

CIE Chromaticity Diagram (Warm White), $T_a=25^\circ\text{C}$, $I_F=65\text{mA}$, CCT=2700K



2H (2.3Step)		3H (3.0step)	
Center point	0.4578 : 0.4101	Center point	0.4578 : 0.4101
Major Axis a	0.0062	Major Axis a	0.0081
Minor Axis b	0.0032	Minor Axis b	0.0042
Ellipse Rotation Angle	54	Ellipse Rotation Angle	54
4H (3.7step)		5H (5.0Step)	
Center point	0.4578 : 0.4101	Center point	0.4578 : 0.4101
Major Axis a	0.0100	Major Axis a	0.0135
Minor Axis b	0.0052	Minor Axis b	0.0070
Ellipse Rotation Angle	54	Ellipse Rotation Angle	54

Mixing order kiting combination

1. Kiting Combination with xx3M

Combination	Reel	FLUX	VF	CIE	Qty
Kiting_a	Reel 1	ALL	E2A	2S	4,000pcs
	Reel 2	ALL	E2A	2S	4,000pcs
Kiting_b	Reel 1	ALL	E2A	2S	4,000pcs
	Reel 2	ALL	E2A	4S	4,000pcs
Kiting_c	Reel 1	ALL	E2A	2S	4,000pcs
	Reel 2	ALL	E2B	2S	4,000pcs
Kiting_d	Reel 1	ALL	E2A	2S	4,000pcs
	Reel 2	ALL	E2B	4S	4,000pcs

2. Kiting Combination with xx4M

Combination	Reel	FLUX	VF	CIE	Qty
Kiting_a	Reel 1	ALL	E2A	2S	4,000pcs
	Reel 2	ALL	E2A	2S	4,000pcs
Kiting_b	Reel 1	ALL	E2A	2S	4,000pcs
	Reel 2	ALL	E2A	5S	4,000pcs
Kiting_c	Reel 1	ALL	E2A	2S	4,000pcs
	Reel 2	ALL	E2B	2S	4,000pcs
Kiting_d	Reel 1	ALL	E2A	2S	4,000pcs
	Reel 2	ALL	E2B	5S	4,000pcs
Kiting_e	Reel 1	ALL	E2A	3S	4,000pcs
	Reel 2	ALL	E2A	3S	4,000pcs
Kiting_f	Reel 1	ALL	E2A	3S	4,000pcs
	Reel 2	ALL	E2A	5S	4,000pcs
Kiting_g	Reel 1	ALL	E2A	3S	4,000pcs
	Reel 2	ALL	E2B	3S	4,000pcs
Kiting_h	Reel 1	ALL	E2A	3S	4,000pcs
	Reel 2	ALL	E2B	5S	4,000pcs

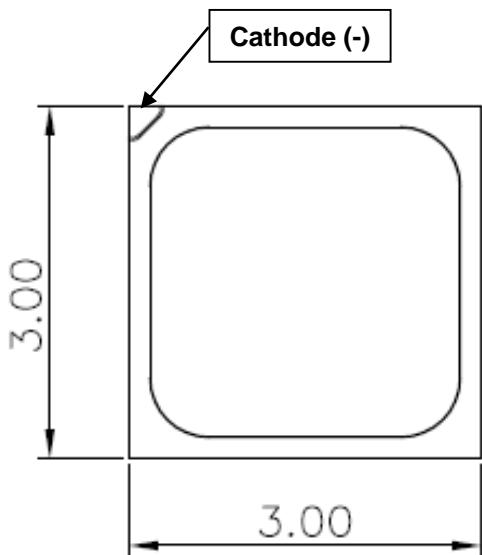
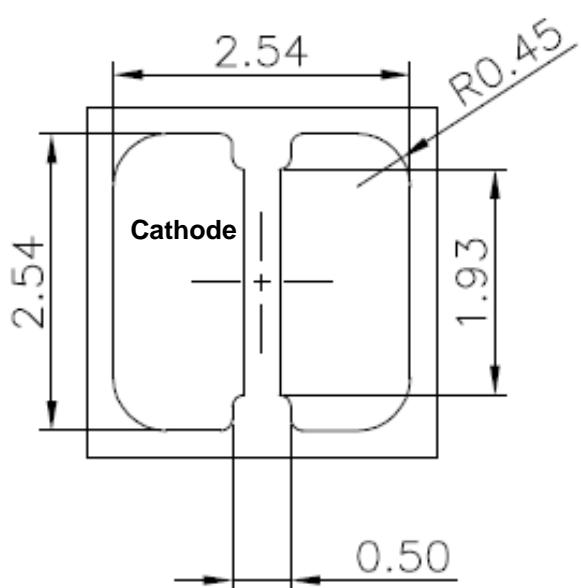
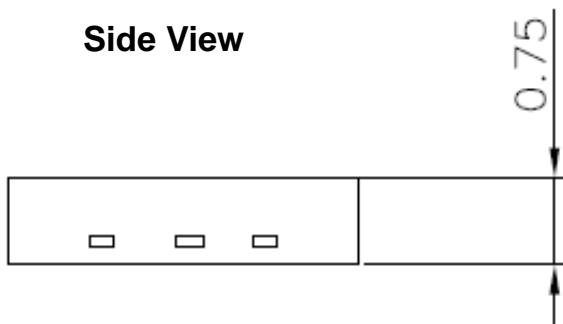
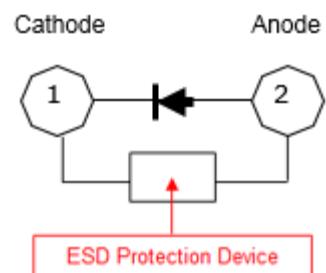
Product Nomenclature

Table 7. Nomenclature example

S	T	W	S	C	1	2	S	-	E	2	H	1	0	0	Z	P	0	0	0	a	b	b	c	c	d	d	e	e	e
X ₁	X ₂	X ₃	X ₄	X ₅	X ₆	X ₇	X ₈	X ₉	X ₁₀	X ₁₁	X ₁₂	X ₁₃	X ₁₄	X ₁₅	X ₁₆	X ₁₇	X ₁₈	X ₁₉	X ₂₀	X ₂₁	X ₂₂	X ₂₃	X ₂₄	X ₂₅	X ₂₆	X ₂₇	X ₂₈	X ₂₉	X ₃₀

Part Number Code	Value	References	Description
X ₁	S	Seoul Semiconductor	Company
X ₂	T	Top lighting	Top View LED series
X ₃	W	White	
X ₄	S	CRI	SunLike
X ₅	C	3030	Package series
X ₆ X ₇	12	Characteristic code	
X ₈	S		Version
X ₉	-		
X ₁₀ X ₁₁	E2	internal code	
X ₁₂ ~X ₂₀	H100ZP000	internal code	
X ₂₁ X ₂₂ X ₂₃	abb	Flux Bin	abb: 225, 240, 255, 270
X ₂₄ X ₂₅	cc	Color Temp.	65=6500K, 57=5700K, 50=5000K, 40=4000K, 30=3000K, 27= 2700K
X ₂₆ X ₂₇	dd	step	3S: 3step single / 3M: 3step Mixing / 4M: 4step Mixing
X ₂₈ X ₂₉ X ₃₀	eee	VF Bin	000: All bin

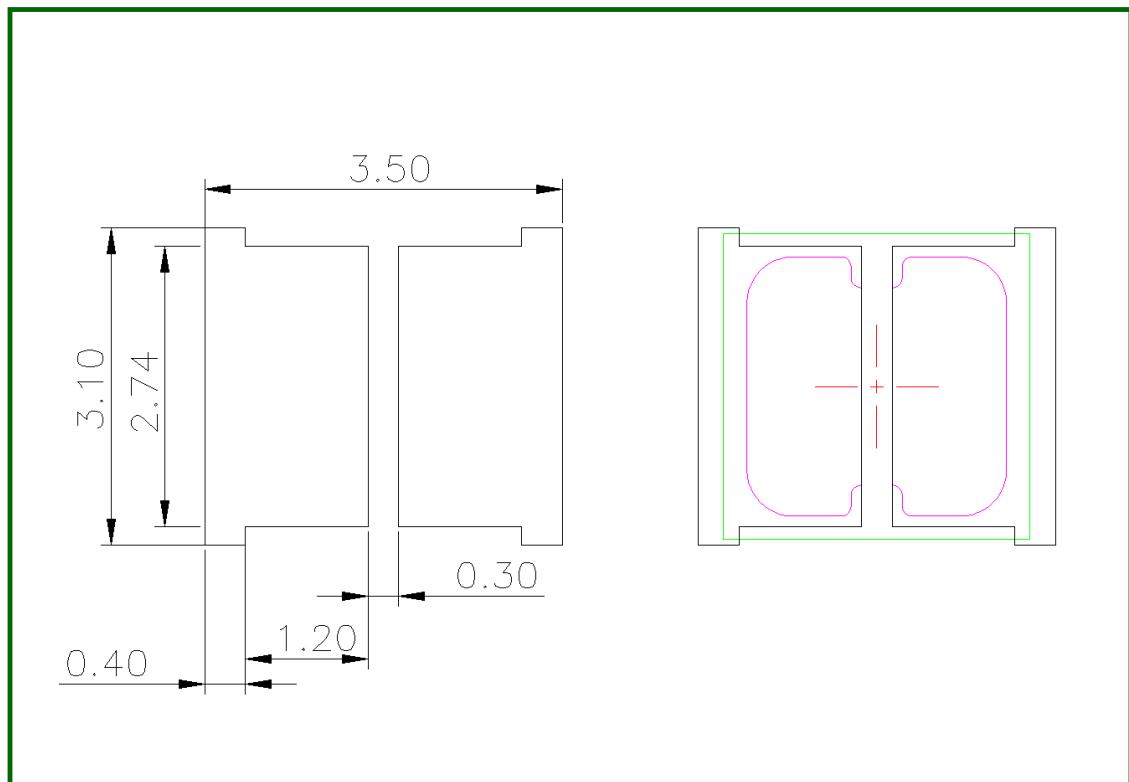
Mechanical Dimensions

Top View**Bottom View****Side View****Circuit**

(1) All dimensions are in millimeters.

(2) Scale : none

(3) Undefined tolerance is $\pm 0.2\text{mm}$

Recommended Solder Pad**Notes :**

- (1) All dimensions are in millimeters.
- (2) Scale : none
- (3) This drawing without tolerances are for reference only
- (4) Undefined tolerance is $\pm 0.1\text{mm}$

Reflow Soldering Characteristics

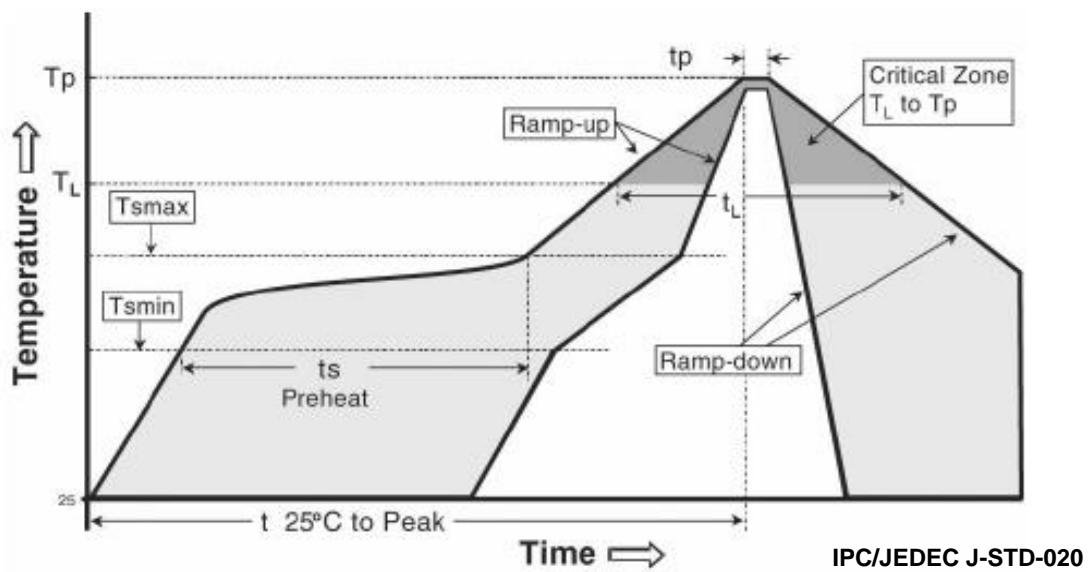


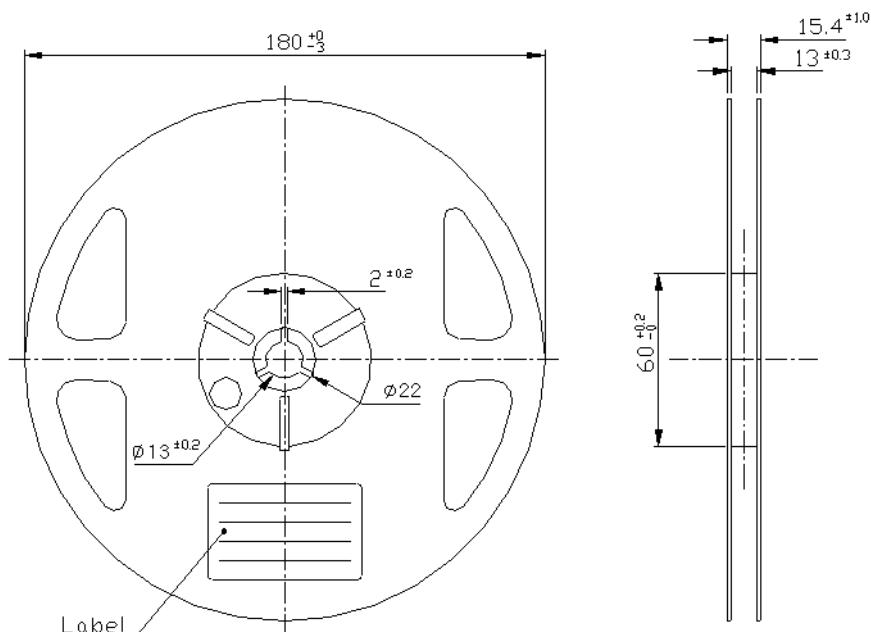
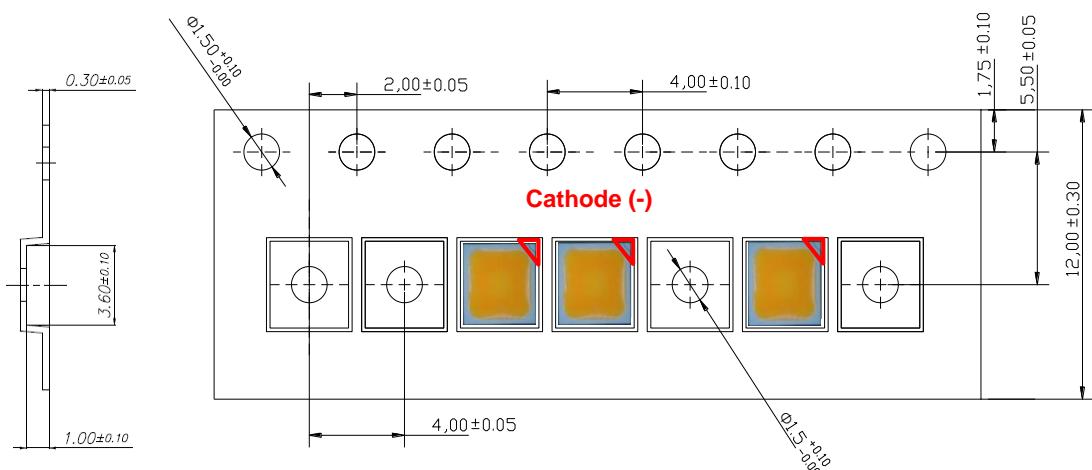
Table 7.

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (Tsmax to Tp)	3° C/second max.	3° C/second max.
Preheat		
- Temperature Min (Tsmin)	100 °C	150 °C
- Temperature Max (Tsmax)	150 °C	200 °C
- Time (Tsmin to Tsmax) (ts)	60-120 seconds	60-180 seconds
Time maintained above:		
- Temperature (TL)	183 °C	217 °C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature (Tp)	215°C	260°C
Time within 5°C of actual Peak Temperature (tp)	10-30 seconds	20-40 seconds
Ramp-down Rate	6 °C/second max.	6 °C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Caution

- (1) Reflow soldering is recommended not to be done more than two times. In the case of more than 24 hours passed soldering after first, LEDs will be damaged.
- (2) Repairs should not be done after the LEDs have been soldered. When repair is unavoidable, suitable tools must be used.
- (3) Die slug is to be soldered.
- (4) When soldering, do not put stress on the LEDs during heating.
- (5) After soldering, do not warp the circuit board.

Emitter Tape & Reel Packing

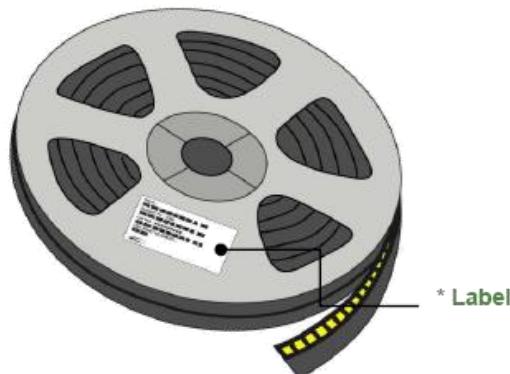


(Tolerance: ±0.2, Unit: mm)

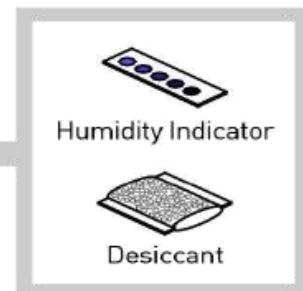
- (1) Quantity : 4,000pcs/Reel
- (2) Cumulative Tolerance : Cumulative Tolerance/10 pitches to be ±0.2mm
- (3) Adhesion Strength of Cover Tape
Adhesion strength to be 0.1-0.7N when the cover tape is turned off from the carrier tape at the angle of 10° to the carrier tape.
- (4) Package : P/N, Manufacturing data Code No. and Quantity to be indicated on a damp proof Package.

Emitter Tape & Reel Packing

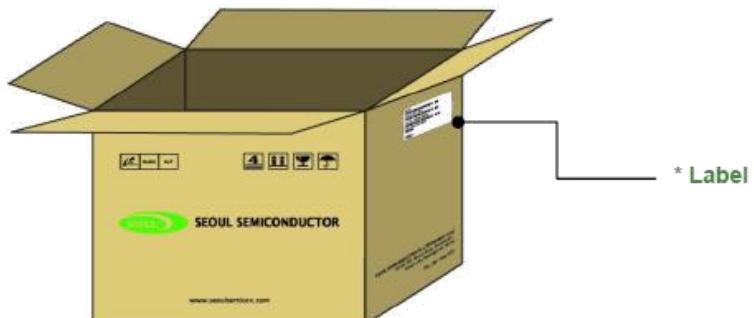
Reel



Aluminum Bag



Outer Box

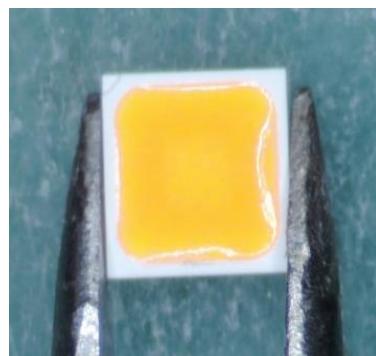


Handling of Silicone Resin for LEDs

(1) During processing, mechanical stress on the surface should be minimized as much as possible. Sharp objects of all types should not be used to pierce the sealing compound.



(2) In general, LEDs should only be handled from the side. By the way, this also applies to LEDs without a silicone sealant, since the surface can also become scratched.



(3) When populating boards in SMT production, there are basically no restrictions regarding the form of the pick and place nozzle, except that mechanical pressure on the surface of the resin must be prevented. This is assured by choosing a pick and place nozzle which is larger than the LED's reflector area.

(4) Silicone differs from materials conventionally used for the manufacturing of LEDs. These conditions must be considered during the handling of such devices. Compared to standard encapsulants, silicone is generally softer, and the surface is more likely to attract dust.

As mentioned previously, the increased sensitivity to dust requires special care during processing. In cases where a minimal level of dirt and dust particles cannot be guaranteed, a suitable cleaning solution must be applied to the surface after the soldering of components.

(5) SSC suggests using isopropyl alcohol for cleaning. In case other solvents are used, it must be assured that these solvents do not dissolve the package or resin.

Ultrasonic cleaning is not recommended. Ultrasonic cleaning may cause damage to the LED.

(6) Please do not mold this product into another resin (epoxy, urethane, etc) and do not handle this product with acid or sulfur material in sealed space.

Precaution for Use

(1) Storage

To avoid the moisture penetration, we recommend store in a dry box with a desiccant.

The recommended storage temperature range is 5°C to 30°C and a maximum humidity of RH50%.

(2) Use Precaution after Opening the Packaging

Use proper SMT techniques when the LED is to be soldered dipped as separation of the lens may affect the light output efficiency.

Pay attention to the following:

a. Recommend conditions after opening the package

- Sealing
- Temperature : 5 ~ 30°C Humidity : less than RH60%

b. If the package has been opened more than 4 week(MSL_2a) or the color of the desiccant changes, components should be dried for 10-24hr at 65±5°C

(3) Do not apply mechanical force or excess vibration during the cooling process to normal temperature after soldering.

(4) Do not rapidly cool device after soldering.

(5) Components should not be mounted on warped (non coplanar) portion of PCB.

(6) Radioactive exposure is not considered for the products listed here in.

(7) Gallium arsenide is used in some of the products listed in this publication.

These products are dangerous if they are burned or shredded in the process of disposal.

It is also dangerous to drink the liquid or inhale the gas generated by such products when chemically disposed of.

(8) This device should not be used in any type of fluid such as water, oil, organic solvent and etc.

When washing is required, IPA (Isopropyl Alcohol) should be used.

(9) When the LEDs are in operation the maximum current should be decided after measuring the package temperature.

Precaution for Use

(10) The appearance and specifications of the product may be modified for improvement without notice.

(11) Long time exposure of sunlight or occasional UV exposure will cause lens discoloration.

(12) VOCs (Volatile organic compounds) emitted from materials used in the construction of fixtures can penetrate silicone encapsulants of LEDs and discolor when exposed to heat and photonic energy. The result can be a significant loss of light output from the fixture. Knowledge of the properties of the materials selected to be used in the construction of fixtures can help prevent these issues.

(13) Attaching LEDs, do not use adhesives that outgas organic vapor.

(14) The driving circuit must be designed to allow forward voltage only when it is ON or OFF. If the reverse voltage is applied to LED, migration can be generated resulting in LED damage.

(15) Similar to most Solid state devices;

LEDs are sensitive to Electro-Static Discharge (ESD) and Electrical Over Stress (EOS). Below is a list of suggestions that Seoul Semiconductor purposes to minimize these effects.

a. ESD (Electro Static Discharge)

Electrostatic discharge (ESD) is the defined as the release of static electricity when two objects come into contact. While most ESD events are considered harmless, it can be an expensive problem in many industrial environments during production and storage. The damage from ESD to an LEDs may cause the product to demonstrate unusual characteristics such as:

- Increase in reverse leakage current lowered turn-on voltage
- Abnormal emissions from the LED at low current

The following recommendations are suggested to help minimize the potential for an ESD event.

One or more recommended work area suggestions:

- Ionizing fan setup
- ESD table/shelf mat made of conductive materials
- ESD safe storage containers

One or more personnel suggestion options:

- Antistatic wrist-strap
- Antistatic material shoes
- Antistatic clothes

Environmental controls:

- Humidity control (ESD gets worse in a dry environment)

Precaution for Use

b. EOS (Electrical Over Stress)

Electrical Over-Stress (EOS) is defined as damage that may occur when an electronic device is subjected to a current or voltage that is beyond the maximum specification limits of the device. The effects from an EOS event can be noticed through product performance like:

- Changes to the performance of the LED package
(If the damage is around the bond pad area and since the package is completely encapsulated the package may turn on but flicker show severe performance degradation.)
- Changes to the light output of the luminaire from component failure
- Components on the board not operating at determined drive power

Failure of performance from entire fixture due to changes in circuit voltage and current across total circuit causing trickle down failures. It is impossible to predict the failure mode of every LED exposed to electrical overstress as the failure modes have been investigated to vary, but there are some common signs that will indicate an EOS event has occurred:

- Damaged may be noticed to the bond wires (appearing similar to a blown fuse)
- Damage to the bond pads located on the emission surface of the LED package
(shadowing can be noticed around the bond pads while viewing through a microscope)
- Anomalies noticed in the encapsulation and phosphor around the bond wires.
- This damage usually appears due to the thermal stress produced during the EOS event.

c. To help minimize the damage from an EOS event Seoul Semiconductor recommends utilizing:

- A surge protection circuit
- An appropriately rated over voltage protection device
- A current limiting device

Company Information

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Company Information

Seoul Semiconductor (www.SeoulSemicon.com) manufacturers and packages a wide selection of light emitting diodes (LEDs) for the automotive, general illumination/lighting, Home appliance, signage and back lighting markets. The company is the world's fifth largest LED supplier, holding more than 10,000 patents globally, while offering a wide range of LED technology and production capacity in areas such as "nPola", "Acrich", the world's first commercially produced AC LED, and "Acrich MJT - Multi-Junction Technology" a proprietary family of high-voltage LEDs.

The company's broad product portfolio includes a wide array of package and device choices such as Acrich and Acrich2, high-brightness LEDs, mid-power LEDs, side-view LEDs, and through-hole type LEDs as well as custom modules, displays, and sensors.

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